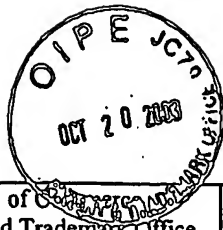


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INFORMATION DISCLOSURE STATEMENT (use several sheets if necessary)				APPLICANT Robert P. Vaudo, et al.			
				FILING DATE July 11, 2003		GROUP TBA	
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EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	NAME	CLASS	SUBCLASS	FILING /PUBLICATION DATE IF APPROPRIATE
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